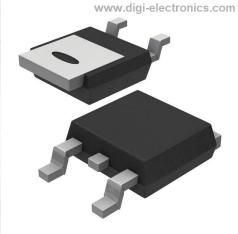


BUK9215-55A,118 Datasheet



DiGi Electronics Part Number Manufacturer Manufacturer Product Number Description

Detailed Description

BUK9215-55A,118-DG

Nexperia USA Inc.

BUK9215-55A,118

MOSFET N-CH 55V 55A DPAK

N-Channel 55 V 55A (Tc) 115W (Tc) Surface Mount D PAK

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BUK9215-55A,118	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
55 V	55A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
4.5V, 10V	13.6mOhm @ 25A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 1mA	48 nC @ 5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±15V	2916 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	115W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
DPAK	TO-252-3, DPAK (2 Leads + Tab), SC-63

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



BUK9215-55A

N-channel TrenchMOS logic level FET 7 April 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	-	62	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	115	W
Static charac	teristics	·					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C		-	11	13.6	mΩ
		V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C		-	-	16.6	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12		-	13	15	mΩ
Dynamic cha	racteristics	·					
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 44 V; T _j = 25 °C; <u>Fig. 9</u>		-	20	-	nC

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N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 62 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	211	mJ

[1] Current is limited by power dissipation chip rating.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	DPAK (SOT428)	mbb076 S
			DPAR (SU1428)	

6. Ordering information

Table 3. Ordering in	formation						
Type number	Package						
	Name	Description	Version				
BUK9215-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

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N-channel TrenchMOS logic level FET

Limiting values 7.

Table 4. **Limiting values**

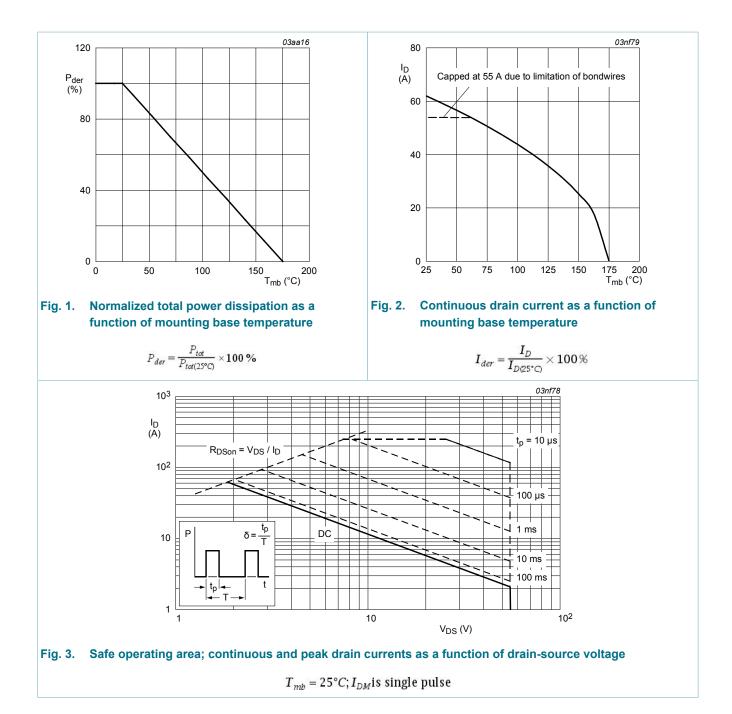
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	55	V
V _{GS}	gate-source voltage			-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	115	W
ID	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2; Fig. 3</u>	[1]	-	62	Α
			[2]	-	55	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[1]	-	44	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 3		-	248	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
ls	source current	T _{mb} = 25 °C	[2]	-	55	А
			[1]	-	62	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	248	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 62 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	211	mJ

Current is limited by power dissipation chip rating.
Continious current is limited by bond wires.

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N-channel TrenchMOS logic level FET

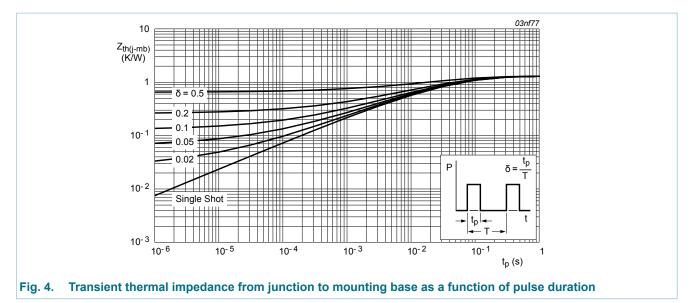


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N-channel TrenchMOS logic level FET

8. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	1.3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W



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N-channel TrenchMOS logic level FET

9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics						
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V	
breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V		
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.3	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V	
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10	1	1.5	2	V	
I _{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA	
		V_{DS} = 55 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA	
I _{GSS} gate leakage current	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	11	13.6	mΩ	
	resistance	V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	16.6	mΩ	
			V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	30	mΩ
	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12		-	13	15	mΩ	
Dynamic ch	naracteristics						
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 44 V; V _{GS} = 5 V;	-	48	-	nC	
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 9</u>	-	6	-	nC	
Q _{GD}	gate-drain charge		-	20	-	nC	
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	2190	2916	pF	
C _{oss}	output capacitance $T_j = 25 \text{ °C}; \text{ Fig. 13}$	T _j = 25 °C; <u>Fig. 13</u>	-	380	450	pF	
C _{rss}	reverse transfer capacitance		-	250	344	pF	
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 5 V;	-	19	-	ns	
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	161	-	ns	
t _{d(off)}	turn-off delay time] [-	138	-	ns	
t _f	fall time		-	165	-	ns	
L _D	internal drain inductance	measured from drain to centre of die	-	2.5	-	nH	

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N-channel TrenchMOS logic level FET

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
L _S	internal source inductance	measured from source lead to source bond pad		-	7.5	-	nH
Source-drain	diode	·					,
V _{SD}	source-drain voltage	I_{S} = 20 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 14</u>		-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs;		-	51	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C		-	102	-	nC

19 R_{DSon}

R_{DSol}. (mΩ) 18

17

16

15

14

13

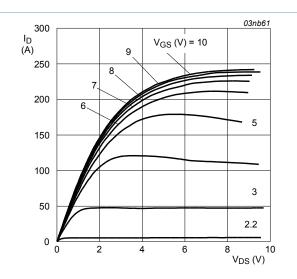
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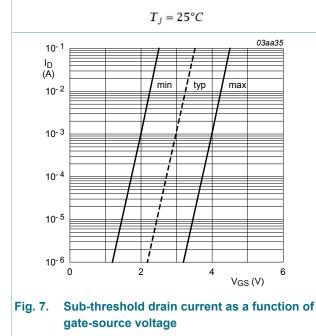
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Fig. 6.

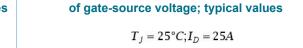
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 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$



9

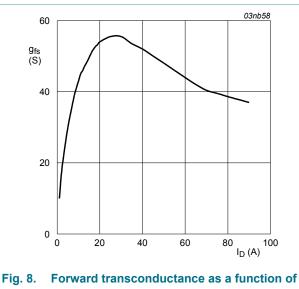
Drain-source on-state resistance as a function

12

V_{GS} (V)

15

6



drain current; typical values

 $T_j = 25^{\circ}C; V_{DS} = 25V$

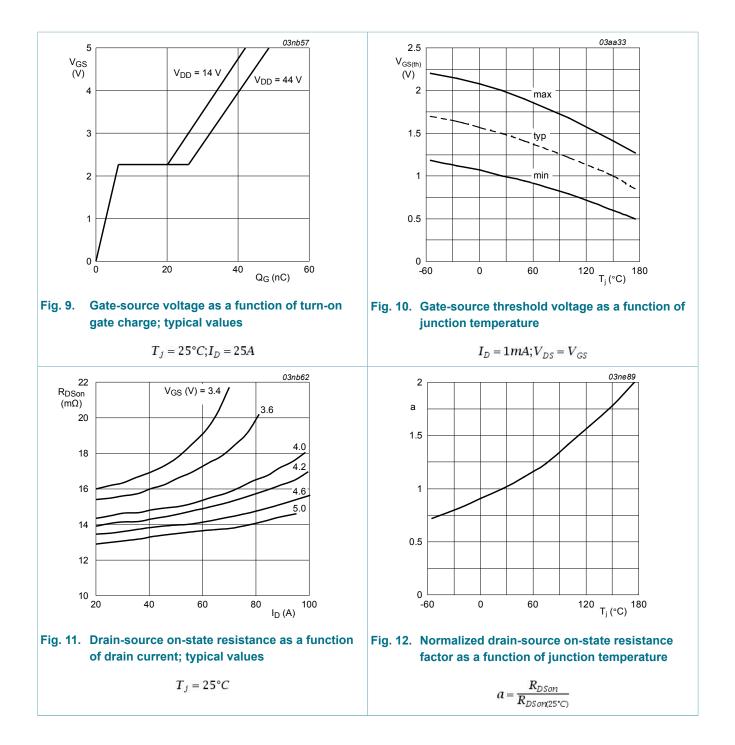
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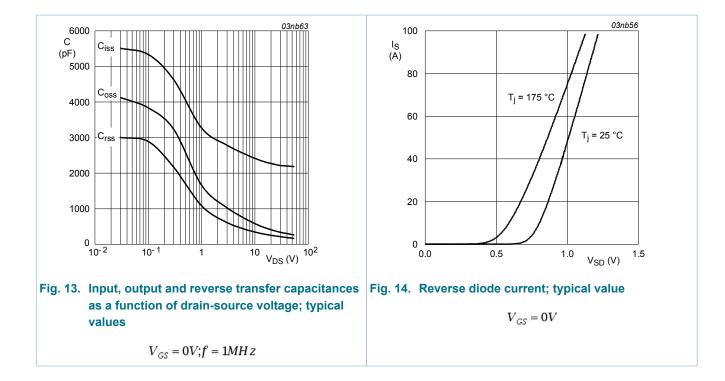
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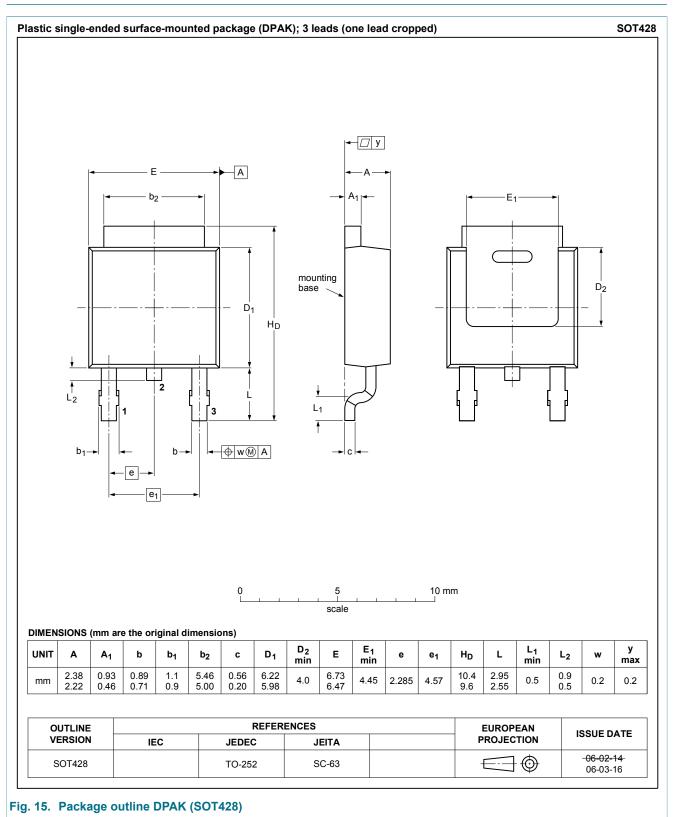
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10. Package outline



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N-channel TrenchMOS logic level FET

11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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N-channel TrenchMOS logic level FET

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